



## Description

The NTR4171P uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.

## General Features

$V_{DS} = -30V, I_D = -4.2A$

$R_{DS(ON)} < 55m\Omega @ V_{GS} = -10V$

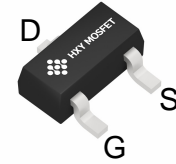
$R_{DS(ON)} < 75m\Omega @ V_{GS} = -4.5V$

## Application

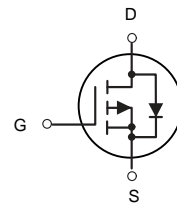
Battery protection

Load switch

Uninterruptible power supply



**SOT-23**



P-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NTR4171P	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	±12	V
$I_D$	Drain Current-Continuous	-4.2	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	-30	A
$P_D$	Maximum Power Dissipation	1.2	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	104	°C/W



**Electrical Characteristics (TA=25°C unless otherwise noted)**

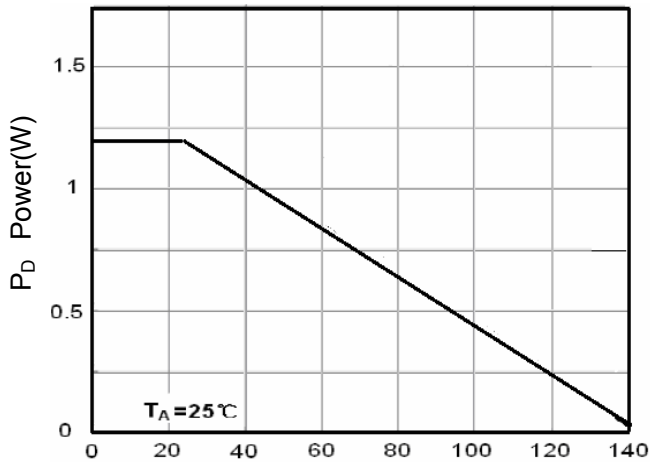
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.2A$	-	45	55	m $\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	-	56	75	m $\Omega$
		$V_{GS}=-2.5V, I_D=-1A$		72	90	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-4.2A$	-	10	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	880	-	PF
Output Capacitance	$C_{oss}$		-	105	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	65	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-4.2A, V_{GS}=-10V, R_{GEN}=6\Omega$	-	7	-	nS
Turn-on Rise Time	$t_r$		-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	$t_f$		-	12	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-4.2A, V_{GS}=-4.5V$	-	8.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=-4.2A$	-	-	-1.2	V

**Notes:**

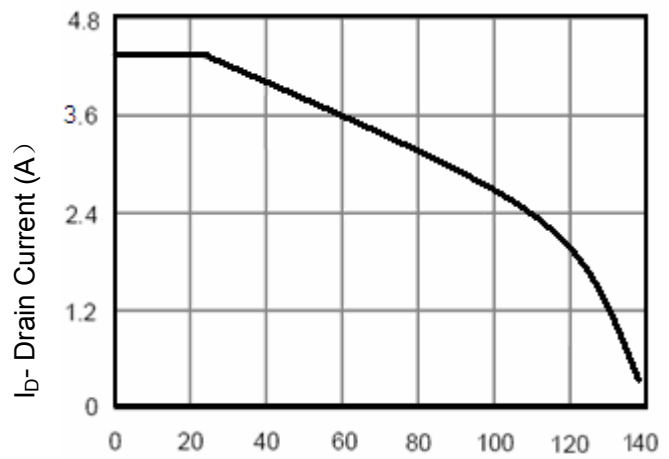
- 1、Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2、Surface Mounted on FR4 Board,  $t \leq 10$  sec.
- 3、Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
- 4、Guaranteed by design, not subject to production



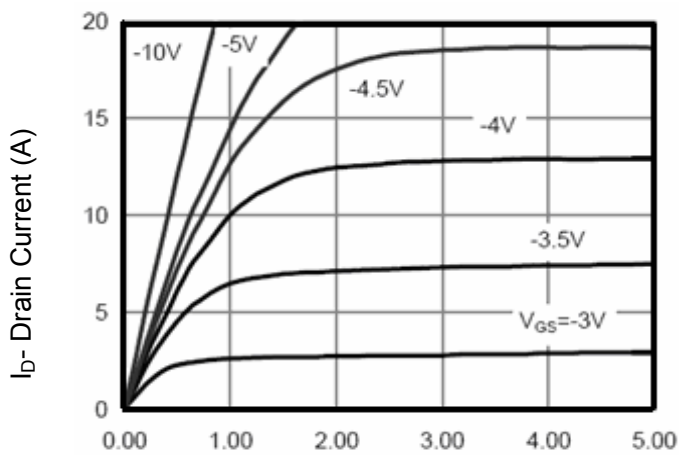
### Typical Electrical and Thermal Characteristics



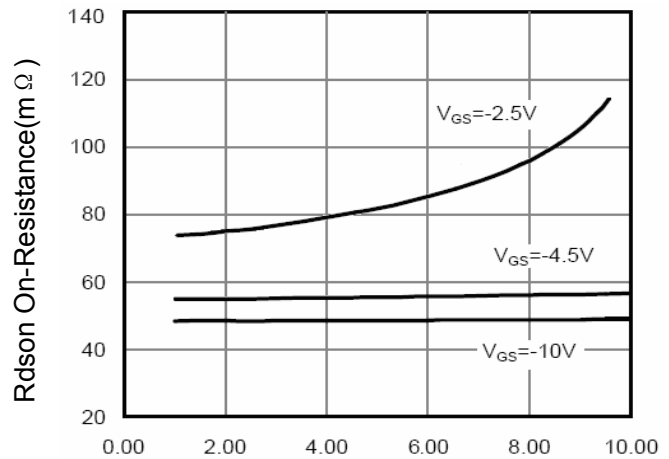
T<sub>J</sub>-Junction Temperature(°C)  
Figure 1 Power Dissipation



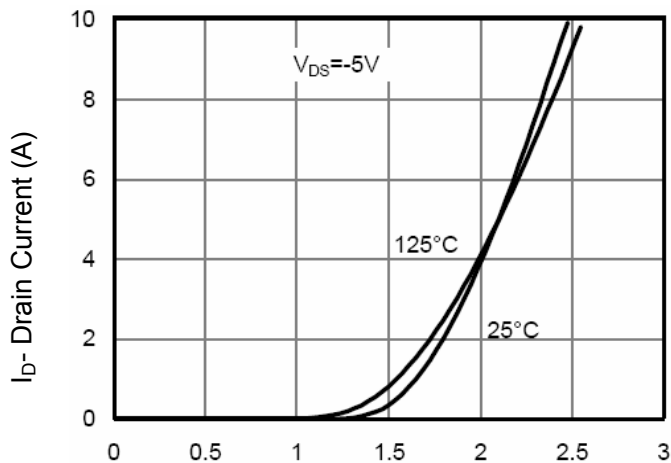
T<sub>J</sub>-Junction Temperature(°C)  
Figure 2 Drain Current



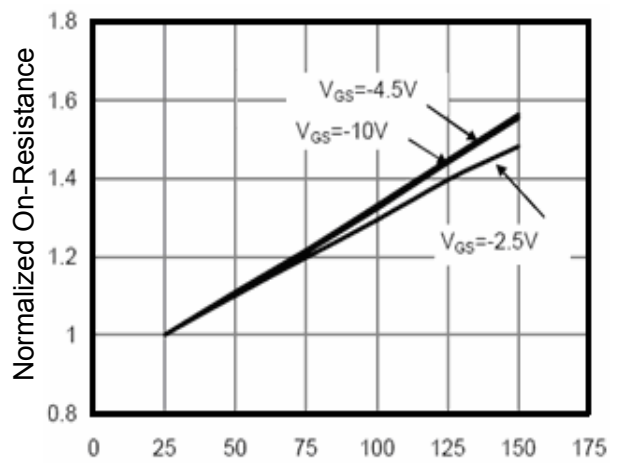
V<sub>DS</sub> Drain-Source Voltage (V)  
Figure 3 Output Characteristics



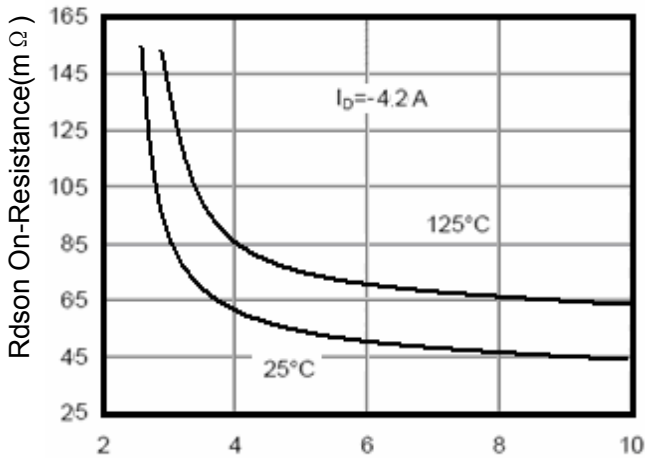
I<sub>D</sub>- Drain Current (A)  
Figure 4 Drain-Source On-Resistance



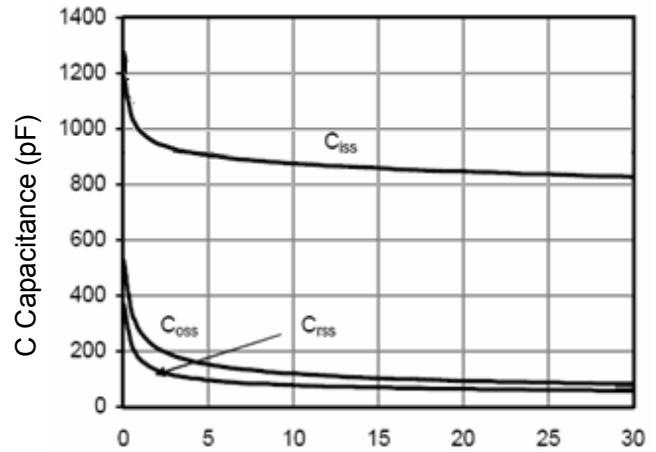
V<sub>GS</sub> Gate-Source Voltage (V)  
Figure 5 Transfer Characteristics



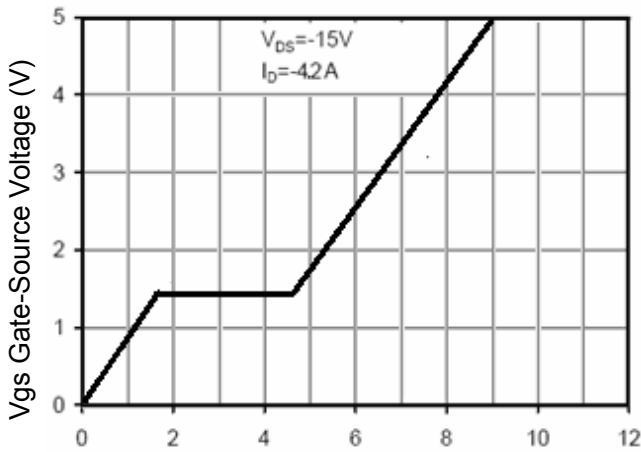
T<sub>J</sub>-Junction Temperature(°C)  
Figure 6 Drain-Source On-Resistance



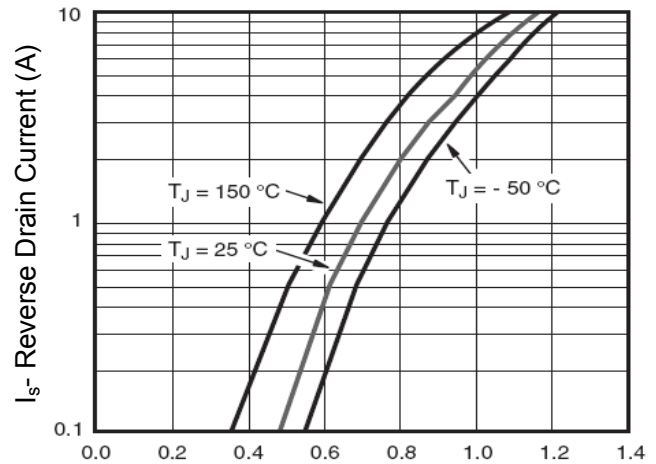
Vgs Gate-Source Voltage (V)  
Figure 7 Rdson vs Vgs



Vds Drain-Source Voltage (V)  
Figure 8 Capacitance vs Vds



Qg Gate Charge (nC)  
Figure 9 Gate Charge



Vsd Source-Drain Voltage (V)  
Figure 10 Source- Drain Diode Forward

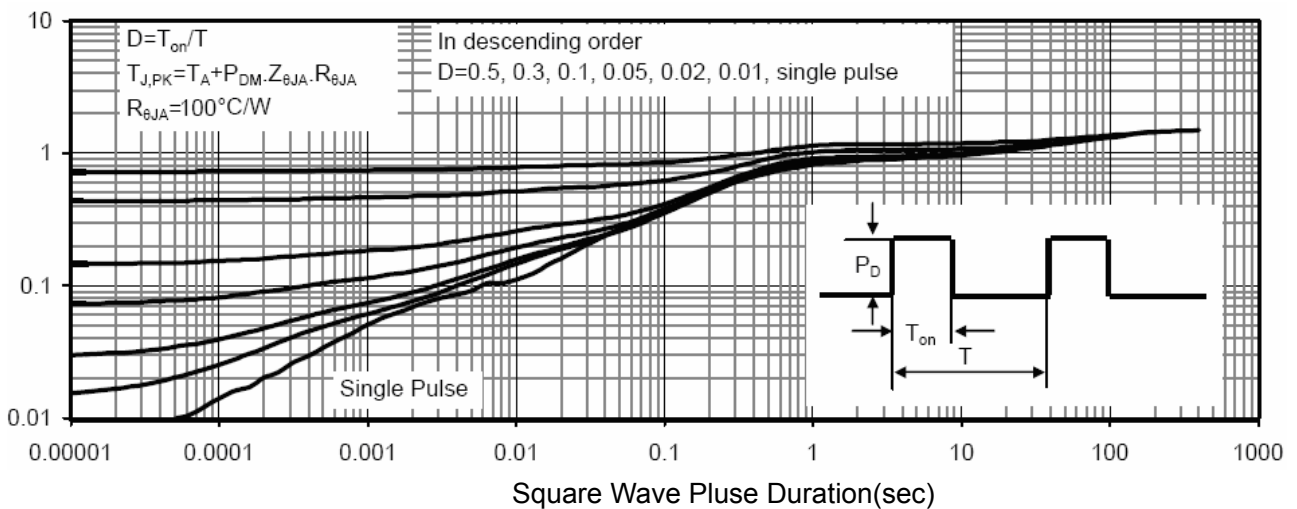
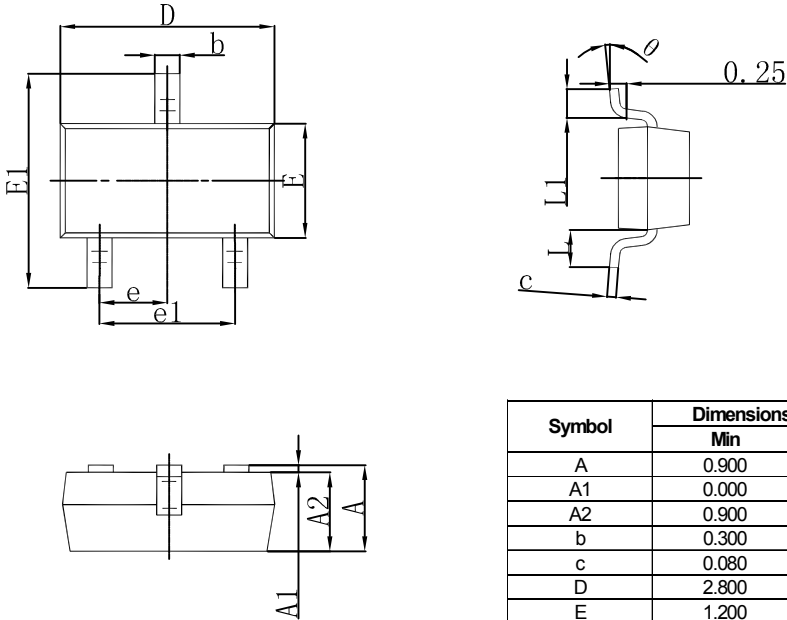


Figure 14 Normalized Maximum Transient Thermal Impedance

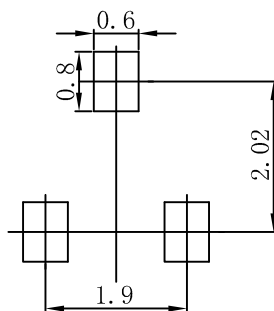


### SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.



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